

**INFORMATION DISCLOSURE CITATION**  
(Use several sheets if necessary)



Docket Number (Optional)

F05-420-US

Application Number

10/564,416

Applicant(s)

Masanobu ANDO, et al.

Filing Date

January 12, 2006

Group Art Unit

Not Yet Assigned

**U.S. PATENT DOCUMENTS**

*EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE

**U.S. PATENT APPLICATION PUBLICATIONS**

*EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
SWL		2002/0171092 A1	11/21/2002	GOETZ, et al.			

**FOREIGN PATENT DOCUMENTS**

EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	Translation	
							YES	NO
SWL		EP 1 280 212 A2	01/29/2003	Europe				
SWL		0 662 739 A1	07/12/1995	Europe				
SWL		11-026812	01/29/1999	Japan				ABS ONLY

**OTHER DOCUMENTS**

(Including Author, Title, Date, Pertinent Pages, Etc.)

SWL		European Search Report dated March 8, 2006

EXAMINER	DATE CONSIDERED
CRANE	6/2006

EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP Section 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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			Applicant(s) <b>Masanobu ANDO, et al.</b>				
			Filing Date <b>January 12, 2006</b>		Group Art Unit <b>Not Yet Assigned</b>		
<b>U.S. PATENT DOCUMENTS</b>							
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<b>U.S. PATENT APPLICATION PUBLICATIONS</b>							
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<b>FOREIGN PATENT DOCUMENTS</b>							
	REF	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	Translation
							YES
<b>OTHER DOCUMENTS</b>				<i>(Including Author, Title, Date, Pertinent Pages, Etc.)</i>			
<i>SWL</i>		Kneissl, et al. "Continuous-wave operation of ultraviolet InGaN/InAlGaN multiple-quantum-well laser diodes", Applied Physics Letters, AIP, American Institute of Physics, Melville, NY, US, Vol. 82, No. 15, April 14, 2003, Pages 2386-2388, XP012033738.					
<i>SWL</i>		Nakamura, et al. " InGaN/GaN/AlGaN-based laser diodes with modulation-doped strained-layer superlattices grown on an epitaxially laterally overgrown GaN substrate", Applied Physics Letter, AIP, American Institute of Physics, Melville, NY, US, Vol. 72, No. 2, January 12, 1998.					
EXAMINER <i>CRANE</i>			DATE CONSIDERED <i>6/2006</i>				
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<b>INFORMATION DISCLOSURE CITATION</b> <i>(Use several sheets if necessary)</i>			ATTY DOCKET NO.	APPLICATION NO. <b>60/964,416</b>		
			F05-420-US	Not Yet Assigned		
			APPLICANT(S) <b>Masanobu ANDO, et al.</b>	SEARCHED <b>19 JAN 2006</b>		
FILING DATE <b>20 APR 2005</b>			GROUP/ART UNIT			
Concurrently Herewith			Not Yet Assigned			

**U.S. PATENT DOCUMENTS**

*EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
<i>SWL</i>		6,100,586	08/08/2000	Chen et al.			
<i>SWL</i>		5,578,839	11/26/1996	Nakamura et al.			

**U.S. PATENT APPLICATION PUBLICATIONS**

*EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE

**FOREIGN PATENT DOCUMENTS**

		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
							YES	NO
<i>SWL</i>		2002-43695	02/08/2002	Japan				<i>ABS</i>
		2003-197969	07/11/2003	Japan				<i>ABS</i>
		2003-101081	04/04/2003	Japan				<i>ABS</i>
		11-46038	02/16/1999	Japan				<i>ABS</i>
<i>SWL</i>		11-16812	01/22/1999	Japan				<i>ABS</i>

**OTHER DOCUMENTS** *(Including Author, Title, Date, Pertinent Pages, Etc.)*

<i>SWL</i>	R.P. Schneider, Jr. et al., "MOVPE growth of InAlGaN-based visible vertical-cavity surface-emitting lasers" Journal of Crystal Growth 124 (1992) 763-771 North-Holland
<i>SWL</i>	S. Keller et al., "Growth of bulk InGaN films and quantum wells by atmospheric pressure metalorganic chemical vapour deposition" Journal of Crystal Growth 170 (1997) 349-352

EXAMINER	DATE CONSIDERED
<i>ORANG</i>	<i>6/2006</i>

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**INFORMATION DISCLOSURE CITATION**  
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ATTY DOCKET NO.  
F05-420-US

APPLICATION NO. 11/4416  
Not Yet Assigned

Masanobu IAR20 Rec'd PCT/PTO 12 JAN 2006

FILING  
Concurrently Herewith

GROUP ART  
Not Yet Assigned

**U.S. PATENT DOCUMENTS**

*EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE

**U.S. PATENT APPLICATION PUBLICATIONS**

*EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE

**FOREIGN PATENT DOCUMENTS**

EXAMINER INITIAL		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
							YES	NO
SWL		2003-229645	08/15/2003	Japan			ABSTRACT	
		2002-16284	01/18/2002	Japan			ABSTRACT	
		2003-234545	08/22/2003	Japan			ABSTRACT	
SWL		2001-160627	06/12/2001	Japan			ABSTRACT	

**OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)**

C.F. Klingshirn, "Semiconductor Optics" Springer, p284-331

SWL			

EXAMINER

CRANE

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6/2006

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